

# Fumihiko Maeda

## List of Publications by Year in descending order

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83  
papers

1,796  
citations

394421

19  
h-index

276875

41  
g-index

83  
all docs

83  
docs citations

83  
times ranked

1931  
citing authors

#	ARTICLE	IF	CITATIONS
1	Microscopic thickness determination of thin graphite films formed on $\text{SiC}$ from quantized oscillation in reflectivity of low-energy electrons. <i>Physical Review B</i> , 2008, 77, .	3.2	330
2	Dependence of electronic properties of epitaxial few-layer graphene on the number of layers investigated by photoelectron emission microscopy. <i>Physical Review B</i> , 2009, 79, .	3.2	246
3	Synchrotron-radiation photoemission study of the high-Tc superconductor $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$ . <i>Physical Review B</i> , 1987, 36, 5686-5689.	3.2	104
4	Surface and bulk core-level shifts of the $\text{Si}(111)-\text{Ag}$ surface: Evidence for a charged $\text{Si}^{3+}$ layer. <i>Physical Review Letters</i> , 1987, 58, 1555-1558.	7.8	99
5	Unoccupied-electronic-band structure of graphite studied by angle-resolved secondary-electron emission and inverse photoemission. <i>Physical Review B</i> , 1988, 37, 4482-4488.	3.2	83
6	Photoemission study of single-crystalline $(\text{La}_{1-x}\text{Sr}_x)_2\text{CuO}_4$ . <i>Physical Review B</i> , 1988, 37, 9788-9791.	3.2	81
7	X-ray standing-wave study of an Sb-terminated $\text{GaAs}(001)-(2\times 4)$ surface. <i>Physical Review B</i> , 1995, 52, 2678-2681.	3.2	53
8	Electronic structure of single-walled carbon nanotubes encapsulating potassium. <i>Physical Review B</i> , 2003, 67, .	3.2	52
9	Sb-induced surface reconstruction on $\text{GaAs}(001)$ . <i>Physical Review B</i> , 1993, 48, 14733-14736.	3.2	46
10	Thickness Determination of Graphene Layers Formed on $\text{SiC}$ Using Low-Energy Electron Microscopy. <i>E-Journal of Surface Science and Nanotechnology</i> , 2008, 6, 107-110.	0.4	46
11	Electronic and surface properties of H-terminated diamond surface affected by $\text{NO}_2$ gas. <i>Diamond and Related Materials</i> , 2010, 19, 889-893.	3.9	46
12	Ultraviolet Photoemission Study of High-Tc Superconductor $(\text{La}_{1-x}\text{Sr}_x)_2\text{CuO}_4$ . <i>Japanese Journal of Applied Physics</i> , 1987, 26, L349-L351.	1.5	40
13	Surface structure of Se-treated $\text{GaAs}(001)$ from angle-resolved analysis of core-level photoelectron spectra. <i>Physical Review B</i> , 1993, 48, 4956-4959.	3.2	33
14	Angle-resolved ultraviolet photoemission study of first stage alkali-metal graphite intercalation compounds. <i>European Physical Journal B</i> , 1988, 70, 349-355.	1.5	30
15	Thin Graphitic Structure Formation on Various Substrates by Gas-Source Molecular Beam Epitaxy Using Cracked Ethanol. <i>Japanese Journal of Applied Physics</i> , 2010, 49, 04DH13.	1.5	30
16	Study of Graphene Growth by Gas-Source Molecular Beam Epitaxy Using Cracked Ethanol: Influence of Gas Flow Rate on Graphitic Material Deposition. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 06GE12.	1.5	23
17	Structural Instability of Transferred Graphene Grown by Chemical Vapor Deposition against Heating. <i>Journal of Physical Chemistry C</i> , 2013, 117, 22123-22130.	3.1	22
18	Anomalous downward band bending induced by selenium passivation of MBE-grown $\text{InAs}(001)$ surfaces. <i>Applied Surface Science</i> , 1997, 117-118, 735-738.	6.1	21

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19	Two-dimensional emission patterns of secondary electrons from graphene layers formed on SiC(0001). Applied Surface Science, 2008, 254, 7596-7599.	6.1	20
20	Selective, Maskless Growth of InSb on Selenium-Treated GaAs by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1994, 33, 698-701.	1.5	19
21	Hydrogen adsorption on single-walled carbon nanotubes studied by core-level photoelectron spectroscopy and Raman spectroscopy. Carbon, 2008, 46, 1903-1908.	10.3	17
22	Epitaxial growth of monolayer MoSe <sub>2</sub> on GaAs. Applied Physics Express, 2016, 9, 115501.	2.4	17
23	GaSb-Growth Study by Realtime Crystal-Growth Analysis System Using Synchrotron Radiation Photoelectron Spectroscopy. Japanese Journal of Applied Physics, 1996, 35, 4457-4462.	1.5	16
24	Real-Time Analysis of GaSb(001) during Sb Desorption by Core-Level Photoelectron Spectroscopy. Physical Review Letters, 1997, 78, 4233-4236.	7.8	15
25	Photocurrent generation of a single-gate graphene p-n junction fabricated by interfacial modification. Nanotechnology, 2015, 26, 385203.	2.6	15
26	Photoelectron spectroscopy on reconstructed GaSb(001). Journal of Electron Spectroscopy and Related Phenomena, 1996, 80, 225-228.	1.7	13
27	Molecular beam epitaxial growth of graphene and ridge-structure networks of graphene. Journal Physics D: Applied Physics, 2011, 44, 435305.	2.8	13
28	Performance of the high-resolution high-flux monochromator for bending magnet beamline BL-1C at the Photon Factory. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2001, 467-468, 573-576.	1.6	12
29	Surface and interface reactions of catalysts for carbon nanotube growth on Si substrates studied by soft X-ray photoelectron spectroscopy. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 24, 19-25.	2.7	12
30	Gate Operation of InAs/AlGaSb Heterostructures with an Atomic-Layer-Deposited Insulating Layer. Applied Physics Express, 2011, 4, 125702.	2.4	12
31	Core-level photoelectron spectroscopy study of interface structure of hydrogen-intercalated graphene on-type 4H-SiC(0001). Physical Review B, 2013, 88, .	3.2	12
32	Molecular beam epitaxial growth of graphene using cracked ethylene Advantage over ethanol in growth. Diamond and Related Materials, 2013, 34, 84-88.	3.9	11
33	Surface core-level shifts of the -Ga surface. Surface Science, 1987, 186, L568-L574.	1.9	10
34	Electronic Band Structure of C8Cs Studied by Highly-Angle-Resolved Ultraviolet Photoelectron Spectroscopy. Journal of the Physical Society of Japan, 1987, 56, 2581-2589.	1.6	10
35	In-induced surface reconstruction on GaSb(001). Physical Review B, 2000, 62, 1615-1618.	3.2	10
36	Modified epitaxy in Co/S/GaAs(001) and comparison with Co/GaAs(001). Journal of Applied Physics, 2001, 90, 1222-1226.	2.5	10

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37	Sb-induced reconstruction on Sb-terminated GaAs(001). <i>Physical Review B</i> , 1999, 60, 10652-10655.	3.2	9
38	Evaluation of Few-Layer Graphene Grown by Gas-Source Molecular Beam Epitaxy Using Cracked Ethanol. <i>E-Journal of Surface Science and Nanotechnology</i> , 2011, 9, 58-62.	0.4	9
39	Surfactant-mediated control of surface morphology for Co epitaxial film on S-passivated semiconducting substrate. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2001, 19, 384.	1.6	8
40	Reaction Products of Co Catalysts in Ethanol-Chemical-Vapor-Deposition Ambient at Low-Pressure Studied by in situ X-Ray Photoelectron Spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2007, 46, L148-L150.	1.5	8
41	Study of Graphene Growth by Gas-Source Molecular Beam Epitaxy Using Cracked Ethanol: Influence of Gas Flow Rate on Graphitic Material Deposition. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 06GE12.	1.5	8
42	A VUV beamline (ABL-3B) for real-time photoelectron spectroscopy at the NTT synchrotron radiation facility. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 1994, 342, 596-599.	1.6	7
43	Synchrotron radiation photoelectron spectroscopy study of bonding at heterointerfaces between InAs nanocrystals and Se-terminated GaAs. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , 1996, 80, 221-224.	1.7	7
44	Sb desorption from Sb/GaAs(001) and GaSb(001) analyzed by core-level photoelectron spectroscopy. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , 1999, 101-103, 293-298.	1.7	7
45	Epitaxy, Modification of Electronic Structures, Overlayer-Substrate Reaction and Segregation in Ferromagnetic Co Films on Se-Treated GaAs(001) Surface. <i>Japanese Journal of Applied Physics</i> , 2000, 39, 4571-4574.	1.5	7
46	Passivation-mediated growth of Co on Se, S and O rich GaAs surfaces: A potential approach to control interface crystallinity and magnetic continuity. <i>Journal of Applied Physics</i> , 2002, 91, 3943-3945.	2.5	7
47	Real-time analysis for MBE by time-resolved core-level photoelectron spectroscopy. <i>Journal of Synchrotron Radiation</i> , 1998, 5, 1026-1028.	2.4	6
48	Work Function Changes of GaAs Surfaces Induced by Se treatment. <i>Japanese Journal of Applied Physics</i> , 1999, 38, 5847-5850.	1.5	6
49	Surface Reactions of Co on SiO <sub>2</sub> thin layer/Si substrate Studied by LEEM and PEEM. <i>E-Journal of Surface Science and Nanotechnology</i> , 2006, 4, 155-160.	0.4	6
50	Synchrotron Radiation Photoelectron Spectroscopy of High-Tc Superconductor Bi-Sr-Ca-Cu-O Single Crystals. <i>Japanese Journal of Applied Physics</i> , 1989, 28, L361-L363.	1.5	5
51	Formation of InSb nanocrystals on Se-terminated GaAs(001). <i>Journal of Crystal Growth</i> , 1995, 150, 863-867.	1.5	5
52	Optical design for a bending-magnet beamline based on a varied-line-spacing plane grating. <i>Journal of Synchrotron Radiation</i> , 1998, 5, 572-574.	2.4	5
53	Photoelectron Spectroscopy of High-Tc Superconductor (La <sub>1-x</sub> Sr <sub>x</sub> ) <sub>2</sub> CuO <sub>4-δ</sub> . <i>Japanese Journal of Applied Physics</i> , 1987, 26, 1013.	1.5	5
54	Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001). <i>Applied Surface Science</i> , 1994, 82-83, 136-140.	6.1	4

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55	Surface termination of GaAs(001) by Sb dimers. <i>Surface Science</i> , 1996, 357-358, 540-544.	1.9	4
56	Submicrometre-area high-energy-resolution photoelectron spectroscopy system. <i>Journal of Synchrotron Radiation</i> , 1998, 5, 1111-1113.	2.4	4
57	Observation of Ga 3d two-hole states from GaAs surfaces. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , 2001, 114-116, 421-425.	1.7	4
58	Growth of few-layer graphene by gas-source molecular beam epitaxy using cracked ethanol. <i>Physica Status Solidi (B): Basic Research</i> , 2010, 247, 916-920.	1.5	4
59	Initial stages of Ag growth on Sb-terminated GaAs(001). <i>Journal of Crystal Growth</i> , 1995, 150, 1164-1168.	1.5	3
60	Real-time observation of alternating growth on GaSb(001) using core-level photoelectron spectroscopy. <i>Applied Surface Science</i> , 1997, 112, 69-74.	6.1	3
61	Photoelectron microspectroscopy observations of a cleaved surface of semiconductor double heterostructure. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1998, 16, 1086-1090.	2.1	3
62	Resonant Photoemission Spectroscopy of Ga3dTwo-Hole States of GaAs. <i>Journal of the Physical Society of Japan</i> , 2000, 69, 1807-1811.	1.6	3
63	Beamline for angle-resolved photoemission spectroscopy at low-temperature constructed at NTT Atsugi R&D Center. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , 2005, 144-147, 1109-1112.	1.7	3
64	Oxide-mediated formation of $\sqrt{3}\times\sqrt{3}$ -FeSi <sub>2</sub> on Si(001) studied by X-ray adsorption near edge structure analysis using SPELEEM. <i>Surface and Interface Analysis</i> , 2008, 40, 1747-1750.	1.8	3
65	Real-time analysis of alternating growth on GaAs(001) by core-level photoelectron spectroscopy. <i>Applied Surface Science</i> , 2000, 162-163, 319-325.	6.1	2
66	Real-time analysis of a surface phase transition of GaAs (001) by core-level photoelectron spectroscopy and photoelectron diffraction. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , 2004, 137-140, 107-112.	1.7	2
67	Molecular beam epitaxial growth of graphene using cracked ethylene. <i>Journal of Crystal Growth</i> , 2013, 378, 404-409.	1.5	2
68	Photoelectron spectroscopy of LnBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-<math>\delta</math></sub> (Ln=Y and Sm). <i>Physica B: Physics of Condensed Matter &amp; C: Atomic, Molecular and Plasma Physics, Optics</i> , 1987, 148, 476-479.	0.9	1
69	MBE growth of InAs and InSb on EuBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-y</sub> superconducting films. <i>Journal of Crystal Growth</i> , 1993, 127, 672-677.	1.5	1
70	Surface reactions of Ga and As on Sb-terminated GaAs(001). <i>Applied Surface Science</i> , 1994, 82-83, 276-283.	6.1	1
71	Water-Immersion-Induced Surface Reactions of EuBa <sub>2</sub> Cu <sub>3</sub> O <sub>y</sub> Thin Films. <i>Japanese Journal of Applied Physics</i> , 1995, 34, 1396-1400.	1.5	1
72	Effect of strain on the chemical bonds in InAs nanocrystals self-organized on GaAs and Se-terminated GaAs surfaces. <i>Applied Surface Science</i> , 2000, 162-163, 625-629.	6.1	1

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73	GaSb(001) 4Å—2-In Surface Structure Studied by Core-Level Photoelectron Spectroscopy and X-Ray Standing-Wave Analysis. Japanese Journal of Applied Physics, 2000, 39, 4351-4354.	1.5	1
74	Very Gradual and Anomalous Oxidation at the Interface of Hydrogen-Intercalated Graphene/4H-SiC(0001). Journal of Physical Chemistry C, 2017, 121, 26389-26396.	3.1	1
75	Formation of Graphene Nanofin Networks on Graphene/SiC(0001) by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 06FD16.	1.5	1
76	Initial stages of InAs deposition on SrF <sub>2</sub> -coated EuBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-<math>\delta</math></sub> thin-film superconductors. Journal of Applied Physics, 1993, 74, 5212-5216.	2.5	0
77	Photoelectron Spectroscopy of $\text{EuBa}_{2}\text{Cu}_{3}\text{O}_{7-\delta}$ Thin Film Surfaces Treated by an Electron Cyclotron Resonance Oxygen Ion Beam. Japanese Journal of Applied Physics, 1995, 34, L433-L436.	1.5	0
78	Throughput Measurement of a Multilayer-Coated Schwarzschild Objective Using Synchrotron Radiation. Optical Review, 2000, 7, 576-578.	2.0	0
79	Surface Reactions of Metal Catalysts for Carbon Nanotubes on an Oxide Thin Layer/Si Substrates Studied by in-situ Micro X-ray Adsorption Spectroscopy using SPELEEM. Materials Research Society Symposia Proceedings, 2006, 967, 1.	0.1	0
80	Surface Reactions of Metal Catalysts in Ethanol-CVD Ambient at Low-pressure Studied by in-situ Photoelectron Spectroscopy. Materials Research Society Symposia Proceedings, 2006, 963, 1.	0.1	0
81	Proper Combination of Catalyst Materials and Ethanol for High Yield in CVD Growth of Carbon Nanotubes. Materials Research Society Symposia Proceedings, 2008, 1081, 1.	0.1	0
82	Formation of Graphene Nanofin Networks on Graphene/SiC(0001) by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 06FD16.	1.5	0
83	Control of surface bonding by realtime monitoring using synchrotron radiation photoelectron spectroscopy. , 1994, , 127-132.		0